

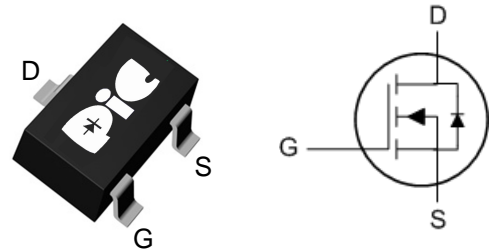
➤ General Description

This PAN0032ANS N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23S package design

➤ SOT-23S



➤ Application

- DC/DC Converters
- Load Switch
- LED Backlighting in LCD TVs

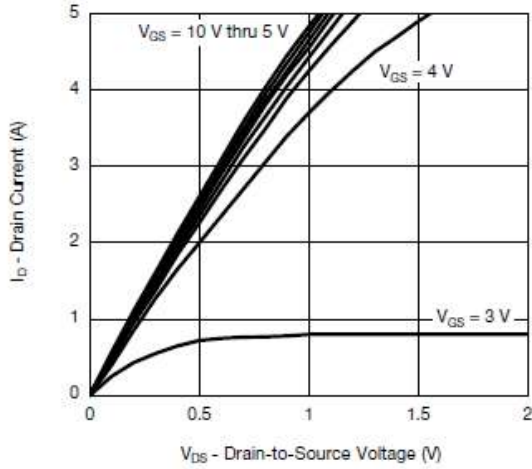
➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	100	V
Gate –Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current($T_J=150^\circ C$)	I_D	$T_C=25^\circ C$	2.3
		$T_C=70^\circ C$	1.8
Pulsed Drain Current	I_{DM}	5	A
Continuous Source Current(Diode Conduction)	I_S	1.6	A
Power Dissipation	P_D	$T_A=25^\circ C$	1.25
		$T_A=70^\circ C$	0.8
Operating Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{STG}	-55/150	$^\circ C$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^\circ C/W$

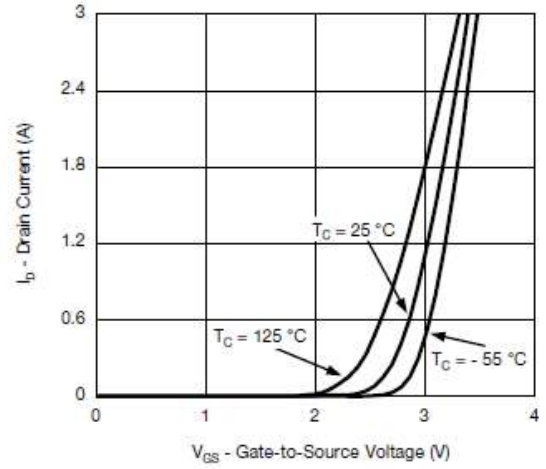
➤ **Electrical Characteristics ($T_A=25^\circ C$ Unless otherwise noted)**

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		2.5	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$			1	uA
		$V_{DS}=80V, V_{GS}=0V$ $T_J=85^\circ C$			10	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 5V, V_{GS}=4.5V$	5			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=2.3A$		265	310	m Ω
		$V_{GS}=4.5V, I_D=1.8A$		275	320	
Forward Transconductance	g_{FS}	$V_{DS}=20V, I_D=1.5A$		2		S
Diode Forward Voltage	V_{SD}	$I_S=1.3A, V_{GS}=0V$		0.85	1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=50V, V_{GS}=4.5V$ $I_D \equiv 1.6A$		2.8	5.8	nC
Gate-Source Charge	Q_{gs}			0.75		
Gate-Drain Charge	Q_{gd}			1.4		
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V$ $f=1MHz$		200		pF
Output Capacitance	C_{oss}			22		
Reverse Transfer Capacitance	C_{rss}			13		
Turn-On Time	$t_{d(on)}$	$V_{DD}=50V, R_L=39\Omega$ $I_D \equiv 1.3A, V_{GEN}=4.5V$ $R_G=1\Omega$		25	50	ns
	t_r			20	50	
Turn-Off Time	$t_{d(off)}$			15	30	
	t_f			10	25	

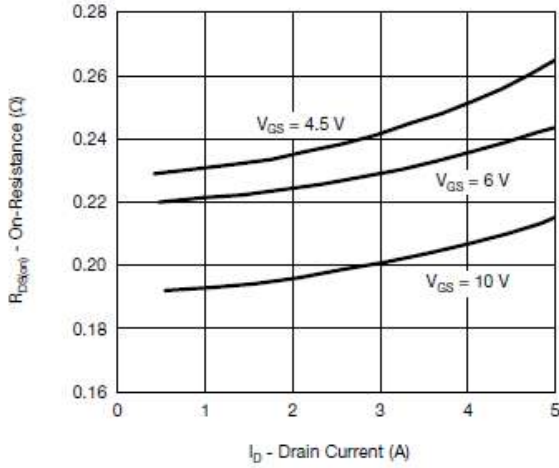
➤ Typical Characteristics



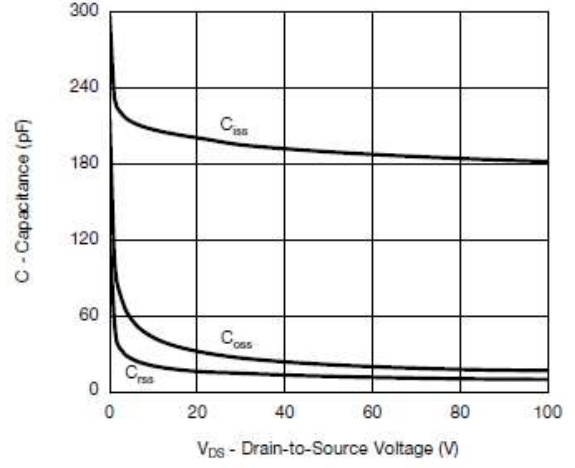
Output Characteristics



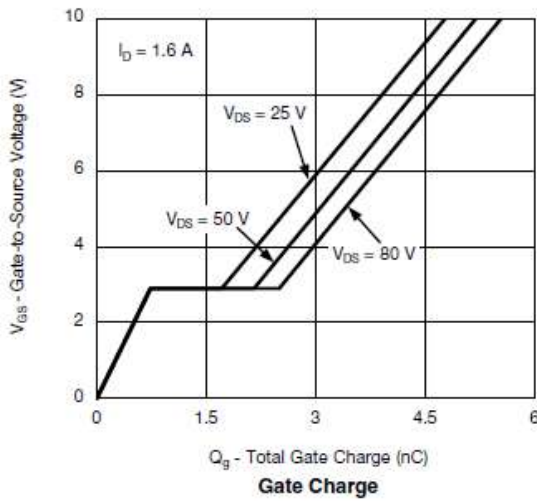
Transfer Characteristics



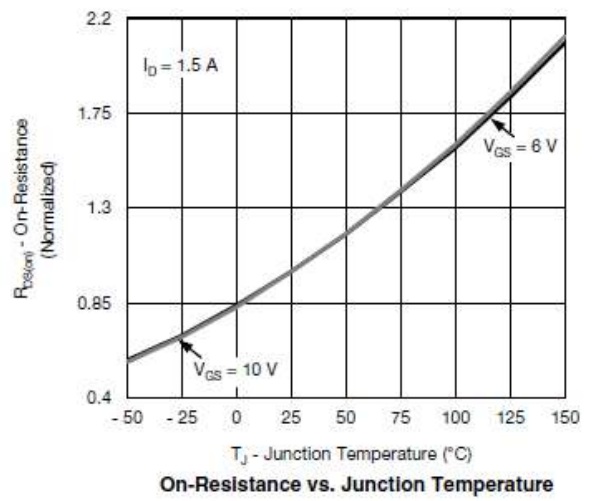
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

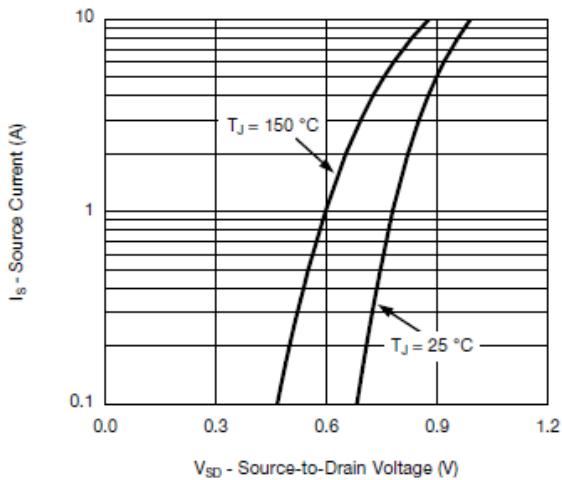


Gate Charge

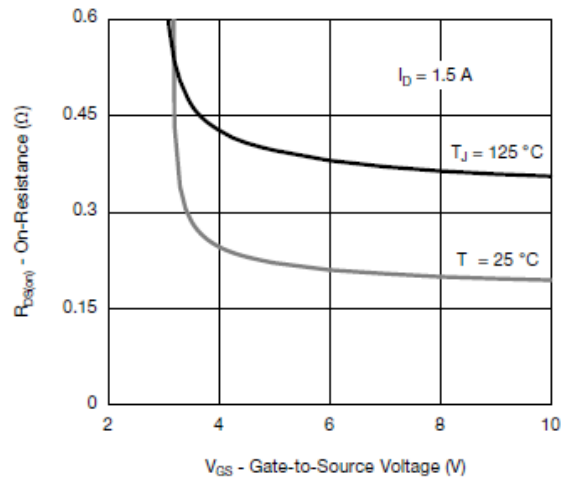


On-Resistance vs. Junction Temperature

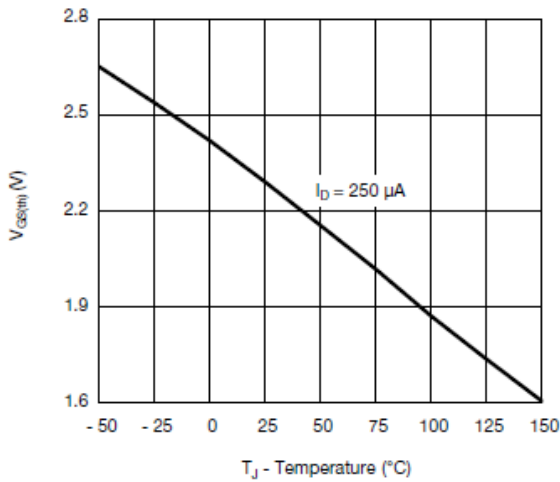
N-Ch 100V Fast Switching MOSFET $V_{DS}=100V$, $I_D=2.3A$, $R_{DS(ON)}=310m\Omega$



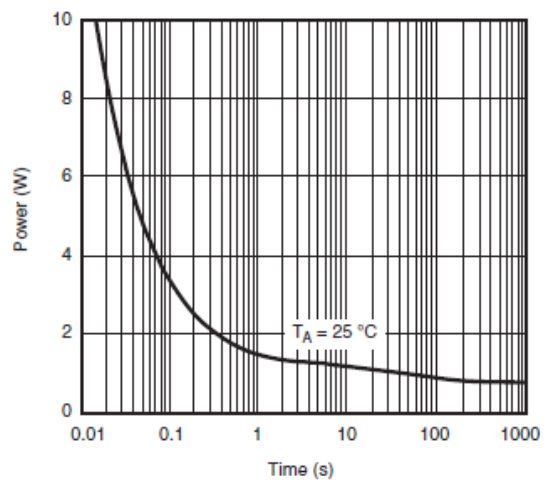
Source-Drain Diode Forward Voltage



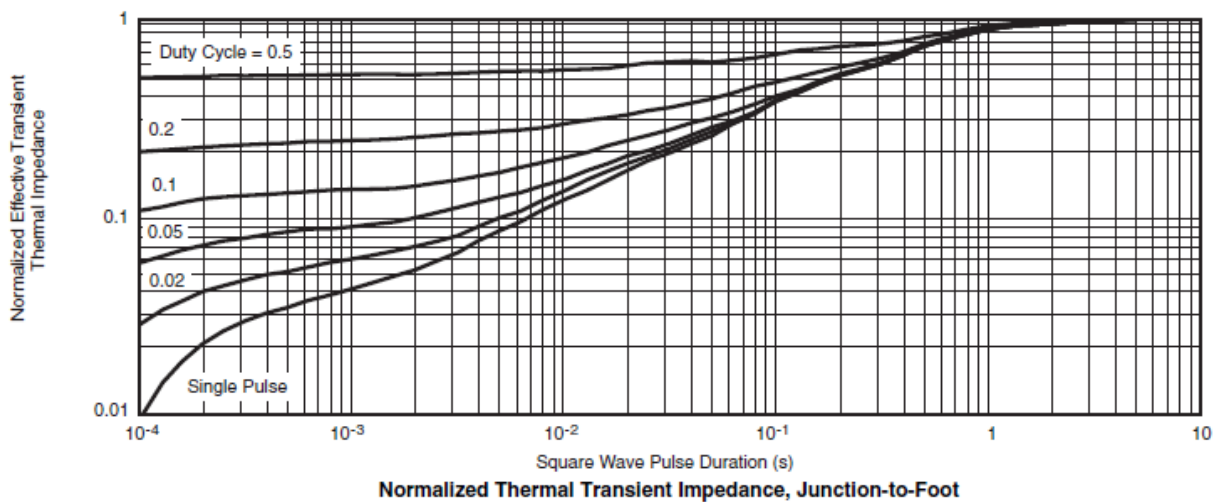
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Foot

➤ Recommand IR Reflow Soldering Thermal Profile

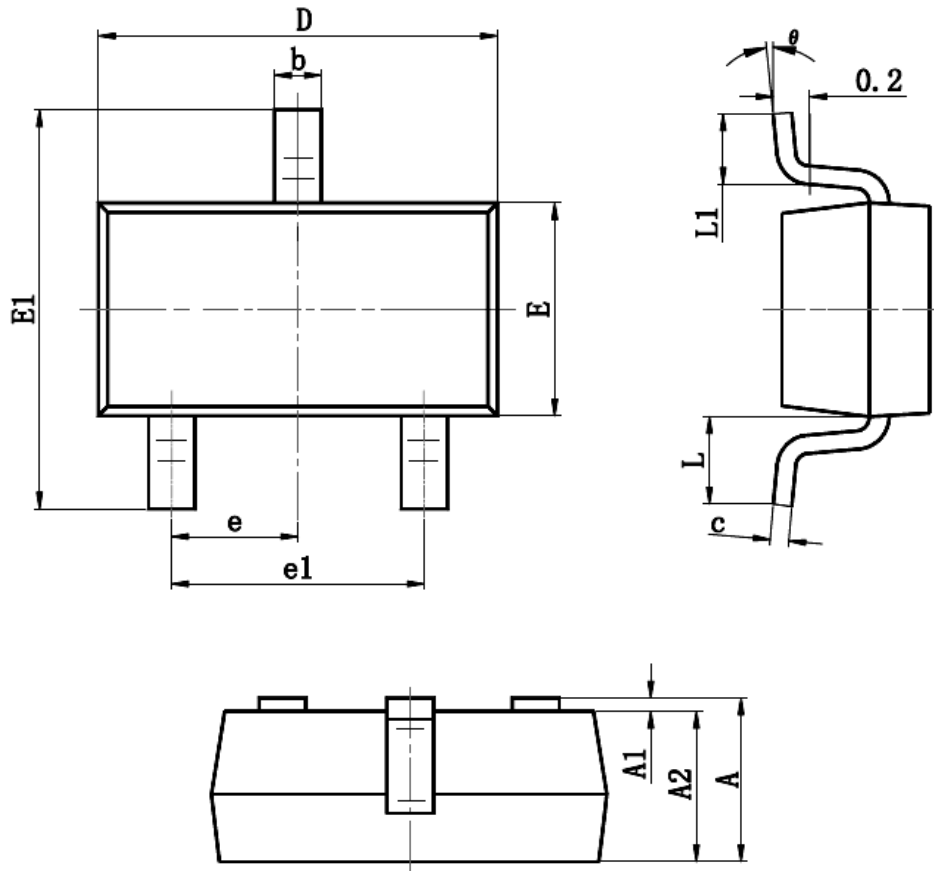


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	150°C
Temperature Max. (T _{smax})	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds
Average Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN0032ANS	SOT-23S Reel	3000 pcs

➤ Package Information (SOT-23S)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°

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